1MBI800UB-120

IGBT Module U-Series 1200V / 800A 1 in one-package

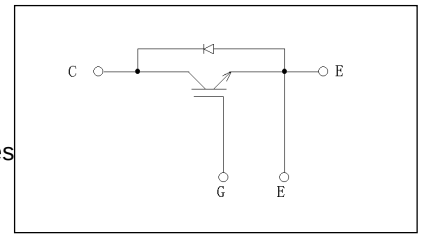
■ Features

· High speed switching
· Voltage drive
· Low inductance module structure

■ Applications

· Inverter for Motor drive
· AC and DC Servo drive amplifier
· Uninterruptible power supply
· Industrial machines, such as Welding machines

■ Equivalent Circuit Schematic



■ Maximum ratings and characteristics

● Absolute maximum ratings (at Tc=25°C unless otherwise specified)

Item		Symbol	Conditions		Rating	Unit
Collector-Emitter voltage		V_{CES}			1200	V
Gate-Emitter voltage		V_{GES}			±20	V
Collector current		I_C	Continuous	Tc=25°C	1200	A
				Tc=80°C	800	
		I_{CP}	1ms	Tc=25°C	2400	
				Tc=80°C	1600	
		-I_C			800	
		-I_C pulse	1ms		1600	
Collector Power Dissipation		P_C	1 device		4805	W
Junction temperature		T_j			+150	℃
Storage temperature		T_{stg}			-40 to +125	
Isolation voltage	between terminal and copper base *1	V_{iso}	AC:1min.		2500	VAC
Screw Torque	Mounting *2				4.5	N·m
	Terminals *2				11.0	
	Terminals *2				1.7	

*1 : All terminals should be connected together when isolation test will be done.

*2 : Recommendable value : Mounting 3.5 to 4.5N·m(M6), Terminal 10.0 to 11.0 N·m(M8), 1.3 to 1.7 N·m(M4)

● Electrical characteristics (at Tj=25°C unless otherwise specified)

Item	Symbols	Conditions		Characteristics Min.	Typ.	Max.	Unit
Zero gate voltage collector current	I_{CES}	V_{GE}=0V, V_{CE}=1200V		–	–	8.0	mA
Gate-Emitter leakage current	I_{GES}	V_{CE}=0V, V_{GE}=±20V		–	–	1600	nA
Gate-Emitter threshold voltage	$V_{GE(th)}$	V_{CE}=20V, I_C=800mA		4.5	6.5	8.5	V
Collector-Emitter saturation voltage	$V_{CE(sat)}$ (terminal)	V_{GE}=15V, I_C=800A	Tj=25°C	–	2.00	2.35	V
			Tj=125°C	–	2.25	–	
	$V_{CE(sat)}$ (chip)		Tj=25°C	–	1.75	2.10	
			Tj=125°C	–	2.00	–	
Input capacitance	C_{ies}	V_{CE}=10V, V_{GE}=0V, f=1MHz		–	90	–	nF
Turn-on time	t_{on}	V_{CC}=600V		–	0.36	1.20	µs
	t_r	I_C=800A		–	0.21	0.60	
	$t_{r(i)}$	V_{GE}=±15V		–	0.03	–	
Turn-off time	t_{off}	R_G= 0.68 Ω		–	0.37	1.00	
	t_f			–	0.07	0.30	
Forward on voltage	V_F (terminal)	V_{GE}=0V	Tj=25°C	–	1.85	2.15	V
		I_F=800A	Tj=125°C	–	1.95	–	
	V_F (chip)		Tj=25°C	–	1.60	1.90	
			Tj=125°C	–	1.70	–	
Reverse recovery time	t_{rr}	I_F=800A		–	–	0.35	µs
Lead resistance, terminal-chip*3	R lead			–	0.30	–	mΩ

*3:Biggest internal terminal resistance among arm.

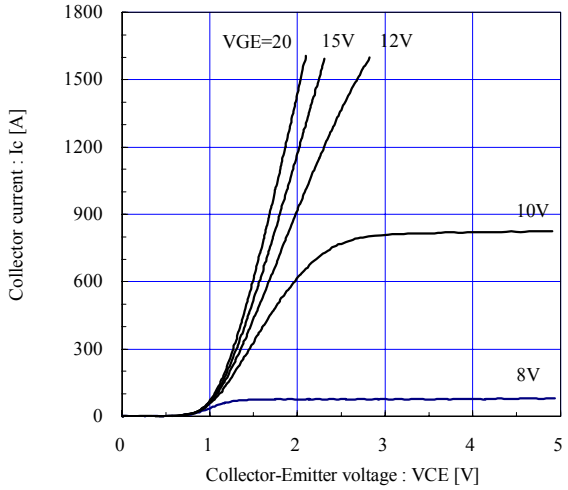
● Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics Min.	Typ.	Max.	Unit
Thermal resistance	Rth(j-c)	IGBT	–	–	0.026	°C/W
	Rth(j-c)	FWD	–	–	0.045	°C/W
Contact Thermal resistance	Rth(c-f)*4	With thermal compound	–	0.0063	–	°C/W

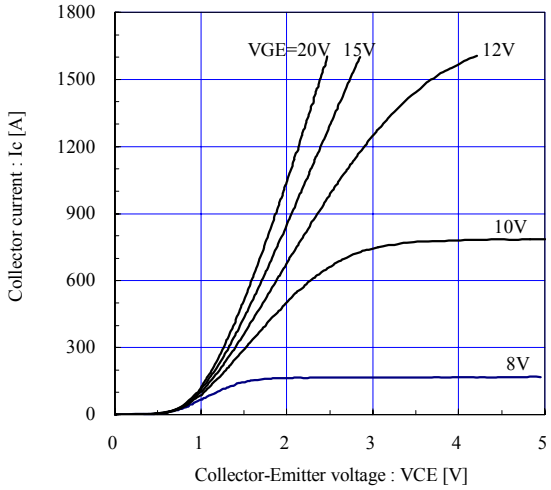
*4 : This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

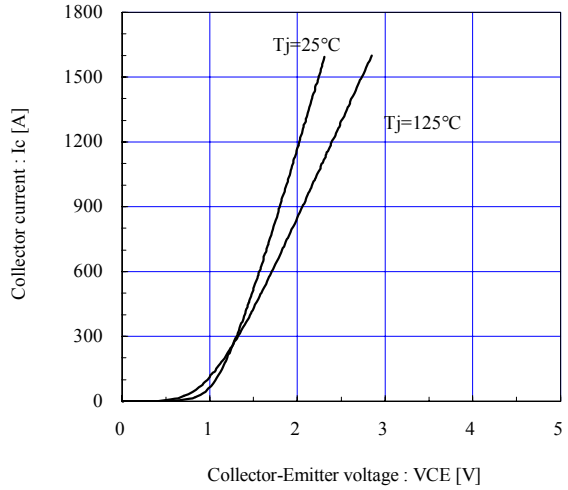
Collector current vs. Collector-Emitter voltage (typ.)
Tj= 25°C / chip



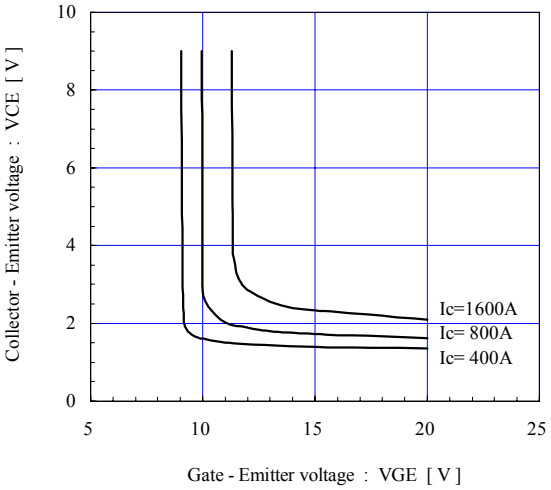
Collector current vs. Collector-Emitter voltage (typ.)
Tj= 125°C / chip



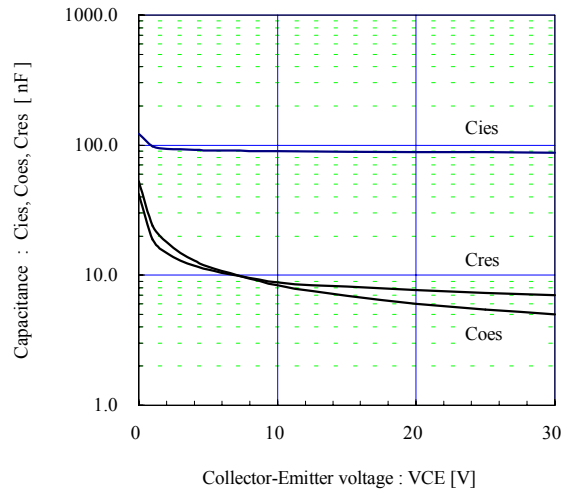
Collector current vs. Collector-Emitter voltage (typ.)
VGE=15V / chip



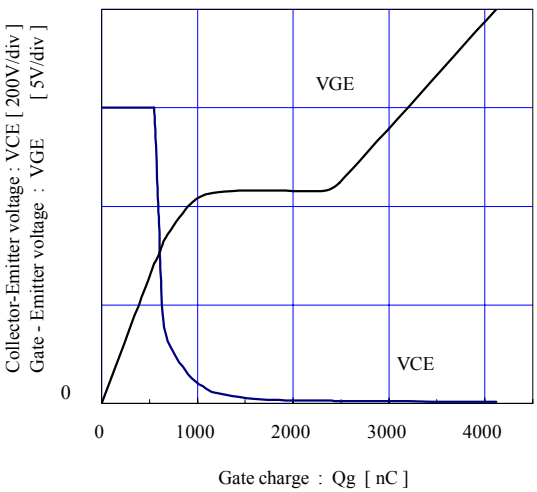
Collector-Emitter voltage vs. Gate-Emitter voltage (typ.)
Tj=25°C / chip



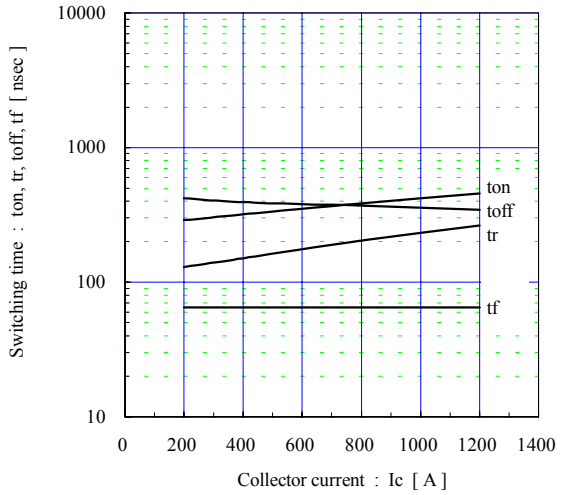
Capacitance vs. Collector-Emitter voltage (typ.)
VGE=0V, f= 1MHz, Tj= 25°C



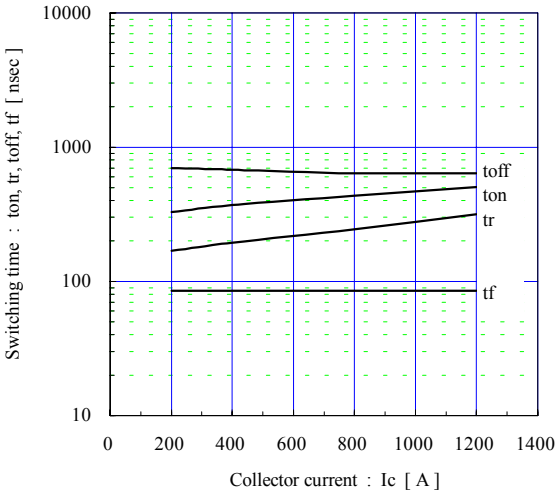
Dynamic Gate charge (typ.)
Vcc=600V, Ic=800A, Tj= 25°C



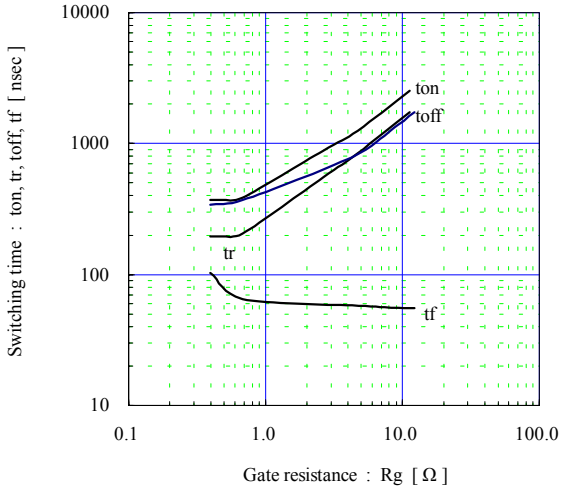
Switching time vs. Collector current (typ.)
Vcc=600V, VGE=±15V, Rg=0.68Ω, Tj= 25°C



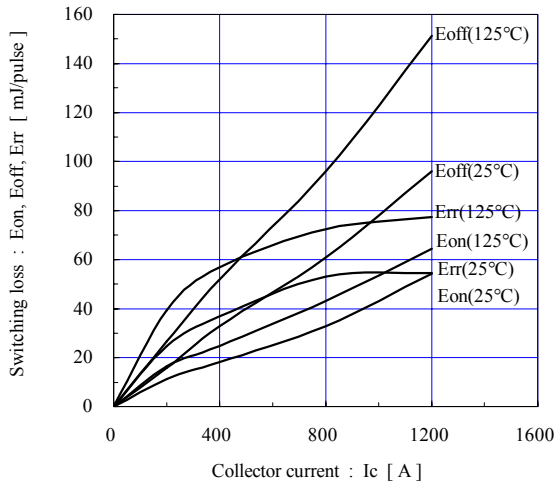
Switching time vs. Collector current (typ.)
Vcc=600V, VGE=±15V, Rg=0.68Ω, Tj=125°C



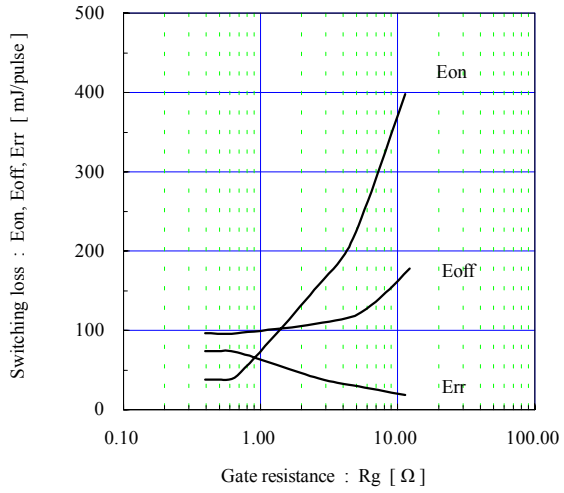
Switching time vs. Gate resistance (typ.)
Vcc=600V, Ic=800A, VGE=±15V, Tj= 25°C



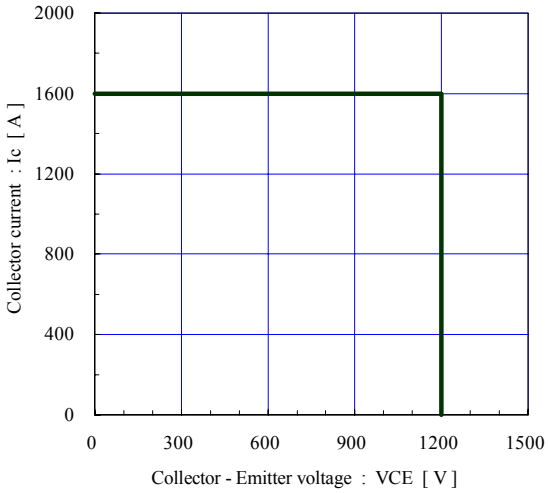
Switching loss vs. Collector current (typ.)
Vcc=600V, VGE=±15V, Rg=0.68Ω



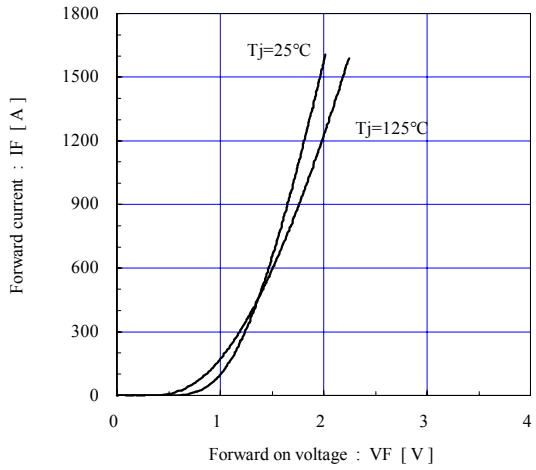
Switching loss vs. Gate resistance (typ.)
Vcc=600V, Ic=800A, VGE=±15V, Tj= 125°C



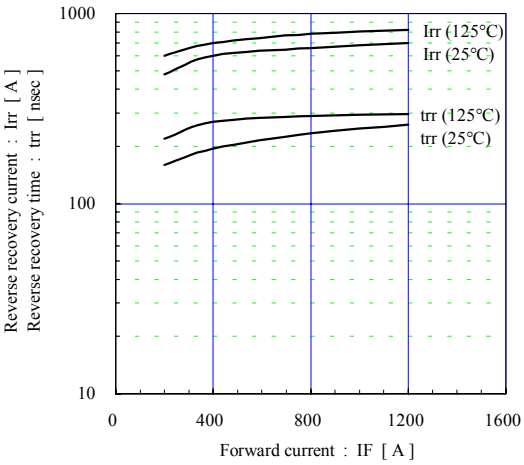
Reverse bias safe operating area (max.)
+VGE=15V,-VGE <= 15V, RG >= 0.68Ω ,Tj <= 125°C



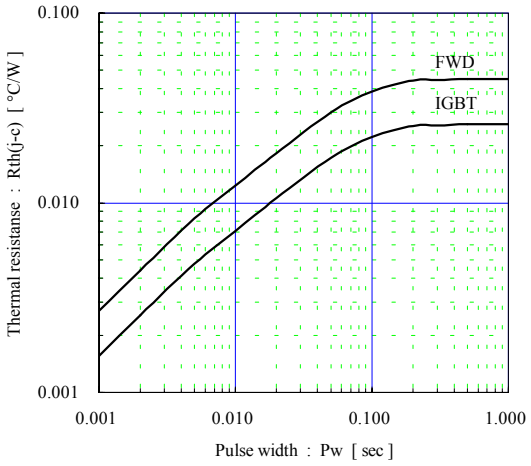
Forward current vs. Forward on voltage (typ.)
chip



Reverse recovery characteristics (typ.)
Vcc=600V, VGE=±15V, Rg=0.68Ω



Transient thermal resistance (max.)



■ Outline Drawings, mm

M138